

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

NISHIMOTO et al

Serial No.: 08/897,839

Filed: July 21, 1997

For: STRESS-ADJUSTED INSULATING )  
FILM FORMING METHOD, )  
SEMICONDUCTOR DEVICE AND )  
METHOD OF MANUFACTURING THE )  
SAME )



Group Art Unit: 2814

Examiner: K. Eaton

ATTENTION AU 2814  
EXPEDITED PROCESSING  
RESPONSE TO FINAL ACTION

2018(4)  
12/13/00  
Cleary

A. Russell  
1-12-01

RESPONSE TO FINAL ACTION OF JULY 5, 2000

Assistant Commissioner for Patents  
Washington, D.C. 20231

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TECHNOLOGY CENTER 2800

Sir:

Responsive to the "final" rejection of July 5, 2000, please amend the captioned application as follows:

IN THE CLAIMS:

Please cancel all pending claims and substitute therefor the following new claims 43-52:

43. A stress-adjusted insulating film forming method for forming a multilayered insulating film on a substrate, said method comprising:

- (a) forming a first insulating layer with a first type of stress;
- (b) forming a conductive interconnection layer on and in